

Corrected accounting of electron-hole scattering in cross-term current equations for Si and SiC

Velme, Enn; Udal, Andres Physica scripta 1999 / Proceedings of 18th Nordic Semiconductor Meeting, Linköping, Sweden, June 7-10, 1998, ISBN 91-87308-71-1, p. 193-197: ill <https://ui.adsabs.harvard.edu/abs/1999PhST...79..193V/abstract>

Corrected accounting of electron-hole scattering in cross-term current equations for Si and SiC

Velme, Enn; Udal, Andres 18th Nordic Semiconductor Meeting, Linköping, June 7-10, 1998 : abstracts 1998 / p. F-88: ill <https://iopscience.iop.org/article/10.1238/Physica.Topical.079a00193>

Interaction of point defects with impurities in the Si-SiO₂ system and its influence on the properties of the interface

Kropman, Daniel; **Melikov, Enn; Lott, Kalju**; Kämer, T.; Heinmaa, I. Gettering and defect engineering in semiconductor technology XIII : CADEST 2009 : proceedings of the XIIIth International Autumn Meeting, Döllnsee-Schorfheide, north of Berlin, Germany, September 26 - October 02, 2009 2010 / p. 145-148 : ill <https://www.sciencedirect.com/science/article/abs/pii/S0040609009014564>